

## IGBT SIP Module (Ultrafast IGBT)



IMS-2

PRODUCT SUMMARY	
OUTPUT CURRENT IN A TYPICAL 20 kHz MOTOR DRIVE	
$V_{CES}$	600 V
$I_{RMS}$ per phase (3.5 kW total) with $T_C = 90\text{ }^\circ\text{C}$	12 $A_{RMS}$
$T_J$	125 $^\circ\text{C}$
Supply voltage	360 $V_{DC}$
Power factor	0.8
Modulation depth (see fig. 1)	115 %
$V_{CE(on)}$ (typical) at $I_C = 10\text{ A}$ , 25 $^\circ\text{C}$	1.56 V
Speed	8 kHz to 30 kHz
Package	SIP
Circuit	Three phase inverter

### FEATURES

- Fully isolated printed circuit board mount package
- Switching-loss rating includes all “tail” losses
- HEXFRED® soft ultrafast diodes
- Optimized for high speed, see fig. 1 for current vs. frequency curve
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


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COMPLIANT**

### DESCRIPTION

The IGBT technology is the key to Vishay’s Semiconductors advanced line of IMS (Insulated Metal Substrate) power modules. These modules are more efficient than comparable bipolar transistor modules, while at the same time having the simpler gate-drive requirements of the familiar power MOSFET. This superior technology has now been coupled to a state of the art materials system that maximizes power throughput with low thermal resistance. This package is highly suited to motor drive applications and where space is at a premium.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		600	V
Continuous collector current, each IGBT	$I_C$	$T_C = 25\text{ }^\circ\text{C}$	20	A
		$T_C = 100\text{ }^\circ\text{C}$	10	
Pulsed collector current	$I_{CM}^{(1)}$		60	
Clamped inductive load current	$I_{LM}^{(2)}$		60	
Diode continuous forward current	$I_F$	$T_C = 100\text{ }^\circ\text{C}$	9.3	
Diode maximum forward current	$I_{FM}$		60	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Isolation voltage	$V_{ISOL}$	$t = 1\text{ min}$ , any terminal to case	2500	$V_{RMS}$
Maximum power dissipation, each IGBT	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	63	W
		$T_C = 100\text{ }^\circ\text{C}$	25	
Operating junction and storage temperature range	$T_J, T_{Stg}$		-40 to +150	$^\circ\text{C}$
Soldering temperature		For 10 s, (0.063" (1.6 mm) from case)	300	
Mounting torque		6-32 or M3 screw	5 to 7 (0.55 to 0.8)	lbf · in (N · m)

#### Notes

- (1) Repetitive rating;  $V_{GE} = 20\text{ V}$ , pulse width limited by maximum junction temperature (see fig. 20)  
 (2)  $V_{CC} = 80\%$  ( $V_{CES}$ ),  $V_{GE} = 20\text{ V}$ ,  $L = 10\text{ }\mu\text{H}$ ,  $R_G = 10\text{ }\Omega$  (see fig. 19)



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TYP.	MAX.	UNITS
Junction to case, each IGBT, one IGBT in conduction	$R_{thJC}$ (IGBT)	-	2.0	°C/W
Junction to case, each DIODE, one DIODE in conduction	$R_{thJC}$ (DIODE)	-	3.0	
Case to sink, flat, greased surface	$R_{thCS}$ (MODULE)	0.10	-	
Weight of module		20	-	g
		0.7	-	oz.

ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$ <sup>(1)</sup>	$V_{GE} = 0\text{ V}$ , $I_C = 250\text{ }\mu\text{A}$	600	-	-	V
Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	$V_{GE} = 0\text{ V}$ , $I_C = 1.0\text{ mA}$	-	0.63	-	V/°C
Collector to emitter saturation voltage	$V_{CE(on)}$	$I_C = 10\text{ A}$	-	1.56	2.1	V
		$I_C = 20\text{ A}$	-	1.84	-	
		$I_C = 10\text{ A}$ , $T_J = 150\text{ °C}$	-	1.56	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	3.0	-	6.0	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	-	- 13	-	mV/°C
Forward transconductance	$g_{fe}$ <sup>(2)</sup>	$V_{CE} = 100\text{ V}$ , $I_C = 10\text{ A}$	11	18	-	S
Zero gate voltage collector current	$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$	-	-	250	$\mu\text{A}$
		$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J = 150\text{ °C}$	-	-	3500	
Diode forward voltage drop	$V_{FM}$	$I_C = 15\text{ A}$	-	1.3	1.7	V
		$I_C = 15\text{ A}$ , $T_J = 150\text{ °C}$	-	1.2	1.6	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 100$	nA

**Notes**

- (1) Pulse width  $\leq 80\text{ }\mu\text{s}$ , duty factor  $\leq 0.1\%$   
(2) Pulse width  $5.0\text{ }\mu\text{s}$ ; single shot



SWITCHING CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q <sub>g</sub>	I <sub>C</sub> = 10 A	V <sub>CC</sub> = 400 V V <sub>GE</sub> = 15 V See fig. 8	-	100	160	nC	
Gate to emitter charge (turn-on)	Q <sub>ge</sub>			-	16	24		
Gate to collector charge (turn-on)	Q <sub>gc</sub>			-	40	55		
Turn-on delay time	t <sub>d(on)</sub>	T <sub>J</sub> = 25 °C I <sub>C</sub> = 10 A, V <sub>CC</sub> = 480 V V <sub>GE</sub> = 15 V, R <sub>G</sub> = 10 Ω Energy losses include "tail" and diode reverse recovery See fig. 9, 10, 11, 18		-	41	-	ns	
Rise time	t <sub>r</sub>			-	13	-		
Turn-off delay time	t <sub>d(off)</sub>			-	96	140		
Fall time	t <sub>f</sub>			-	110	160		
Turn-on switching loss	E <sub>on</sub>			-	0.26	-		mJ
Turn-off switching loss	E <sub>off</sub>	-	0.18	-				
Total switching loss	E <sub>ts</sub>	-	0.44	0.7				
Turn-on delay time	t <sub>d(on)</sub>	T <sub>J</sub> = 150 °C I <sub>C</sub> = 10 A, V <sub>CC</sub> = 480 V V <sub>GE</sub> = 15 V, R <sub>G</sub> = 10 Ω Energy losses include "tail" and diode reverse recovery See fig. 9, 10, 11, 18		-	39	-	ns	
Rise time	t <sub>r</sub>			-	15	-		
Turn-off delay time	t <sub>d(off)</sub>			-	220	-		
Fall time	t <sub>f</sub>			-	160	-		
Total switching loss	E <sub>ts</sub>			-	0.74	-		mJ
Input capacitance	C <sub>ies</sub>	V <sub>GE</sub> = 0 V	V <sub>CC</sub> = 30 V f = 1.0 MHz See fig. 7	-	2100	-	pF	
Output capacitance	C <sub>oes</sub>			-	110	-		
Reverse transfer capacitance	C <sub>res</sub>			-	34	-		
Diode reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	See fig. 14	I <sub>F</sub> = 15 A V <sub>R</sub> = 200 V di/dt = 200 A/μs	-	42	60	ns
		T <sub>J</sub> = 125 °C			-	74	120	
Diode peak reverse recovery charge	I <sub>rr</sub>	T <sub>J</sub> = 25 °C	See fig. 15		-	4.0	6.0	A
		T <sub>J</sub> = 125 °C			-	6.5	10	
Diode reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	See fig. 16		-	80	180	nC
		T <sub>J</sub> = 125 °C			-	220	600	
Diode peak rate of fall of recovery during t <sub>b</sub>	dl <sub>(rec)</sub> M/dt	T <sub>J</sub> = 25 °C	See fig. 17	-	188	-	A/μs	
		T <sub>J</sub> = 125 °C		-	160	-		

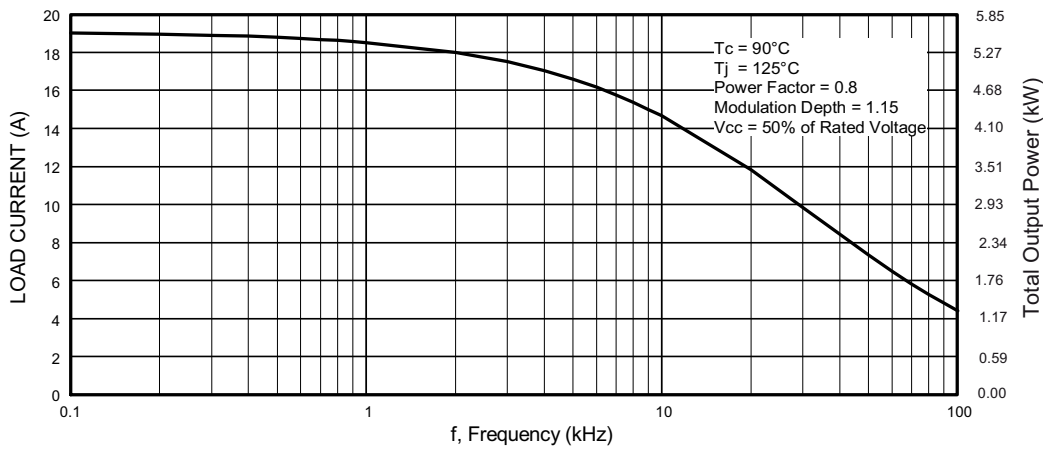


Fig. 1 - Typical Load Current vs. Frequency  
(Load Current =  $I_{RMS}$  of Fundamental)

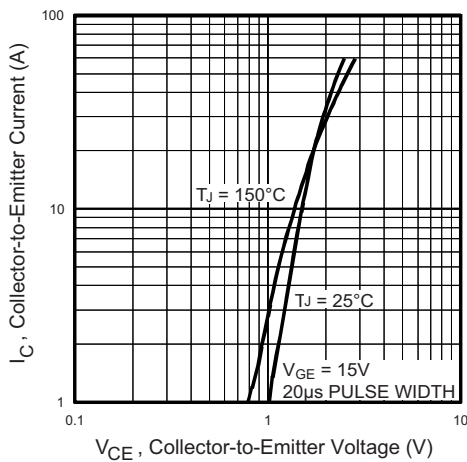


Fig. 2 - Typical Output Characteristics

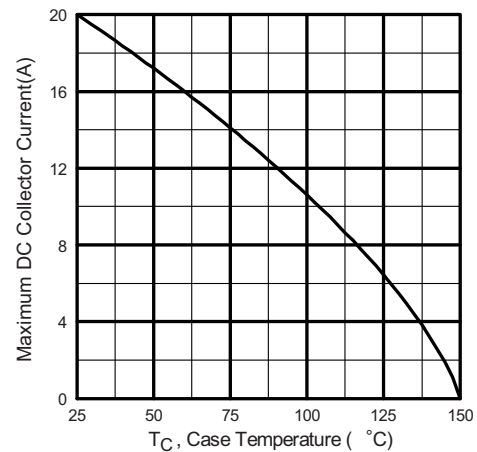


Fig. 4 - Maximum Collector Current vs. Case Temperature

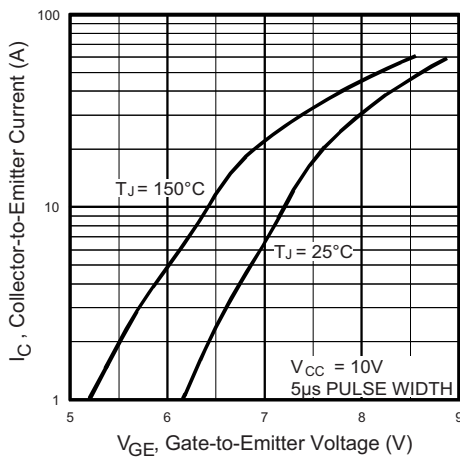


Fig. 3 - Typical Transfer Characteristics

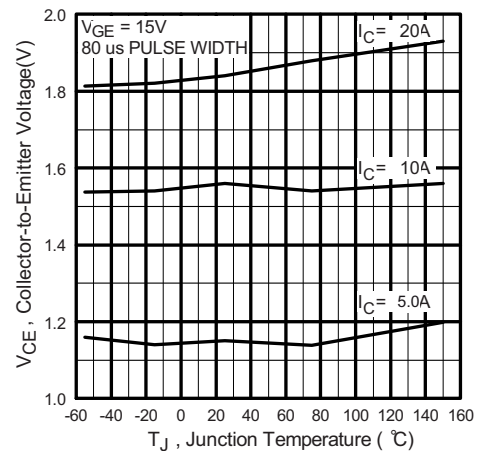


Fig. 5 - Typical Collector to Emitter Voltage vs. Junction Temperature

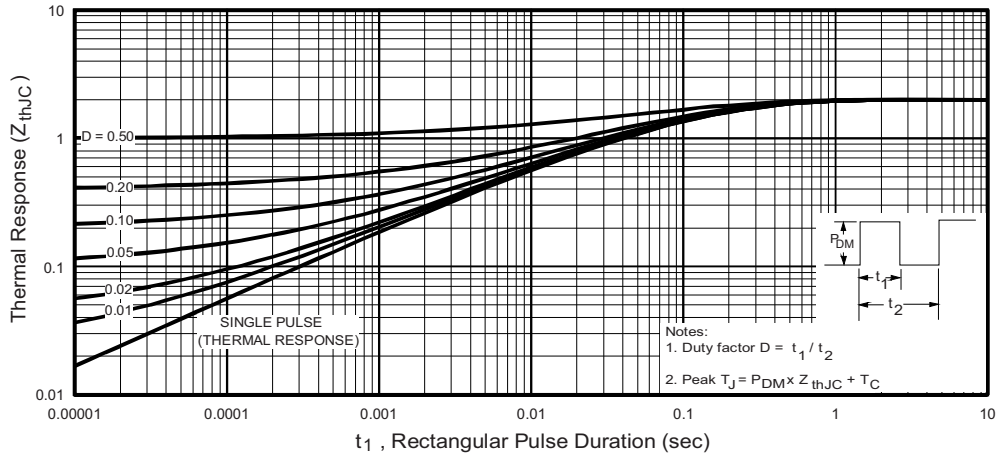


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction to Case

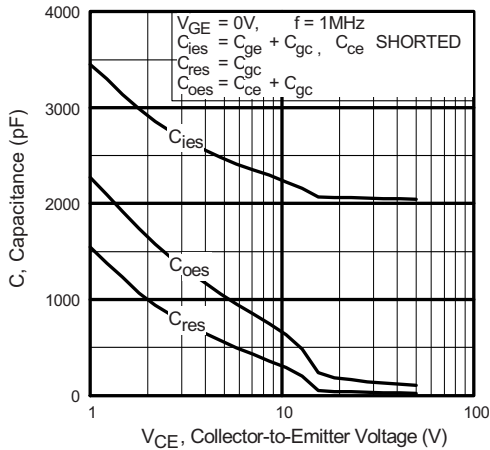


Fig. 7 - Typical Capacitance vs. Collector to Emitter Voltage

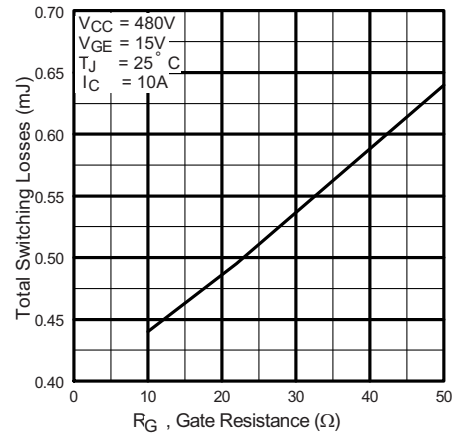


Fig. 9 - Typical Switching Losses vs. Gate Resistance

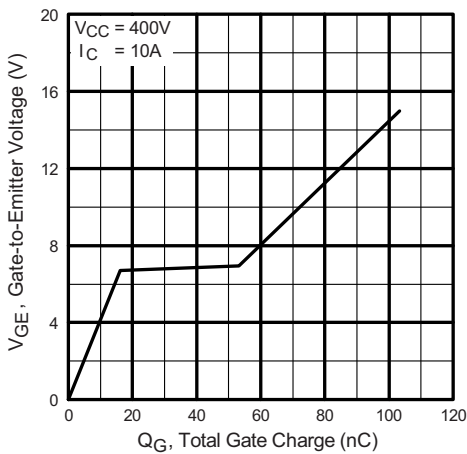


Fig. 8 - Typical Gate Charge vs. Gate to Emitter Voltage

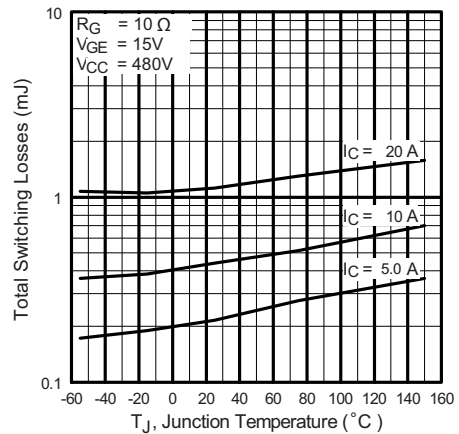


Fig. 10 - Typical Switching Losses vs. Junction Temperature

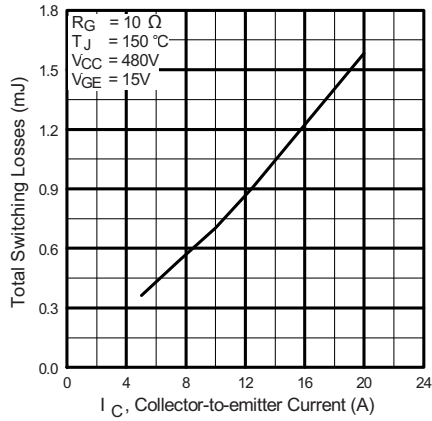


Fig. 11 - Typical Switching Losses vs. Collector to Emitter Current

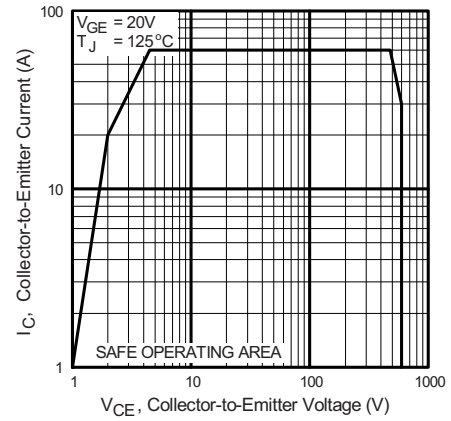


Fig. 12 - Turn-Off SOA

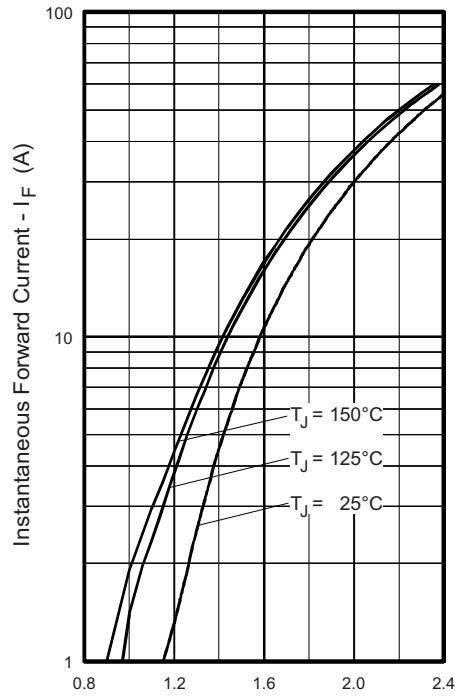


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

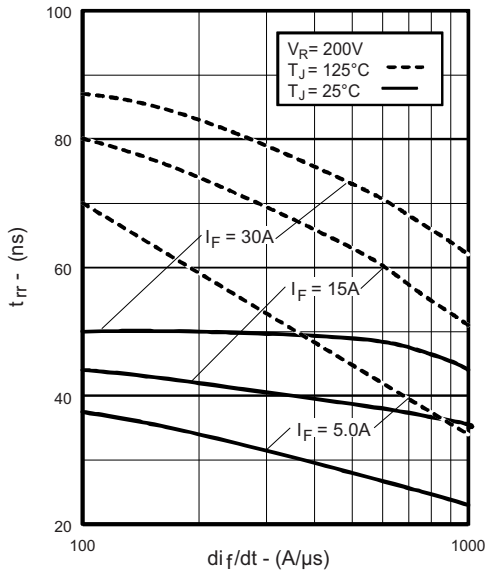


Fig. 14 - Typical Reverse Recovery Time vs.  $di_F/dt$

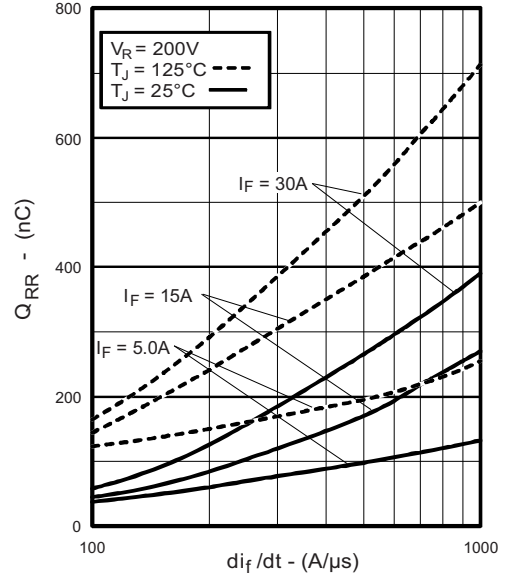


Fig. 16 - Typical Stored Charge vs.  $di_F/dt$

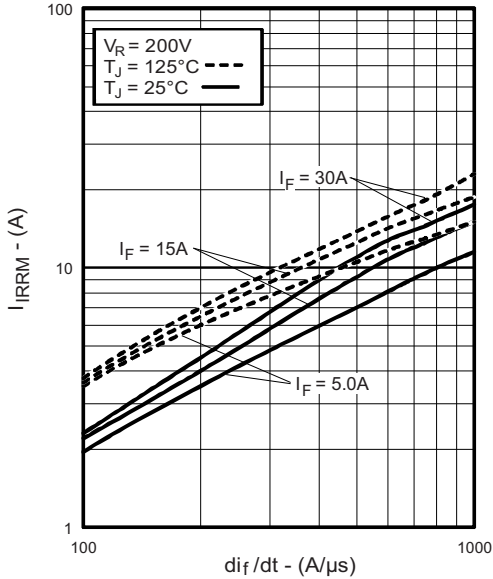


Fig. 15 - Typical Recovery Current vs.  $di_F/dt$

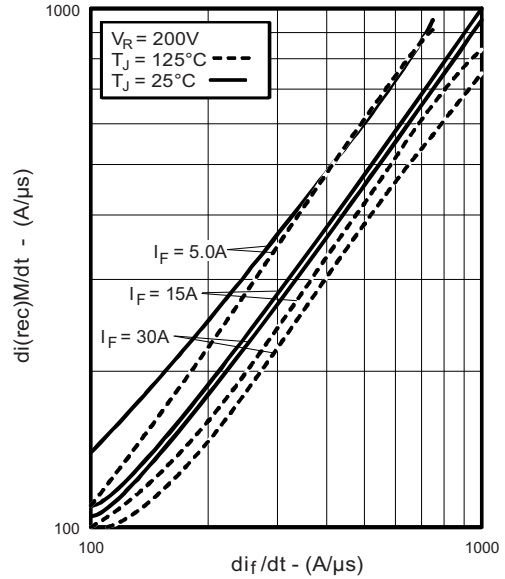


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs  $di_F/dt$



Fig. 18 - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$

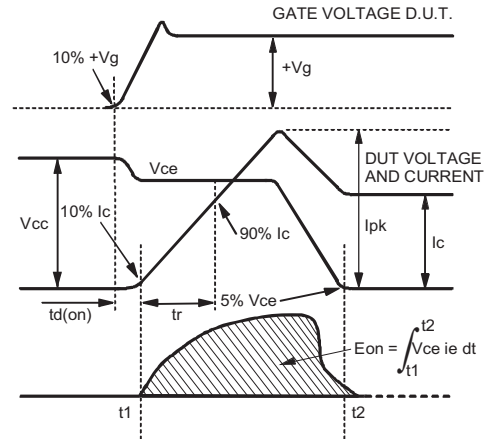


Fig. 20 - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$

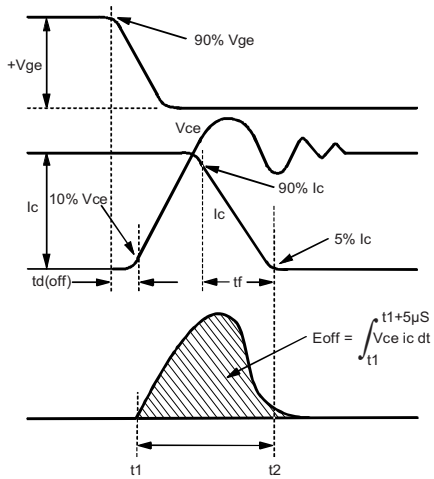


Fig. 19 - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$

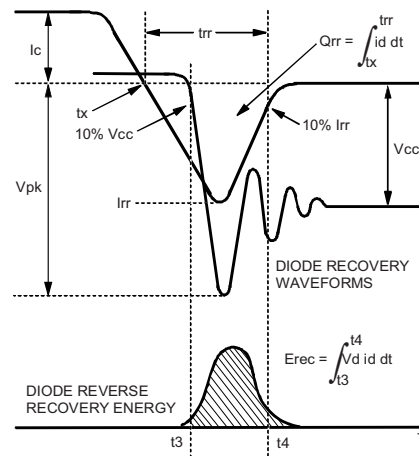


Fig. 21 - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

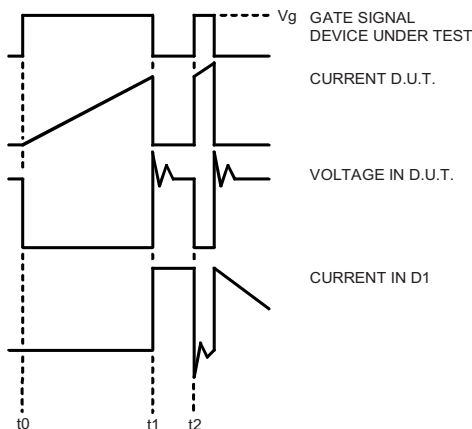


Fig. 18e - Macro Waveforms for Figure 18a's Test Circuit



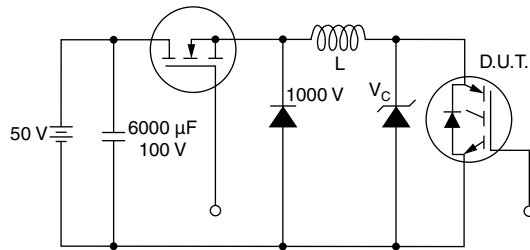


Fig. 19 - Clamped Inductive Load Test Circuit

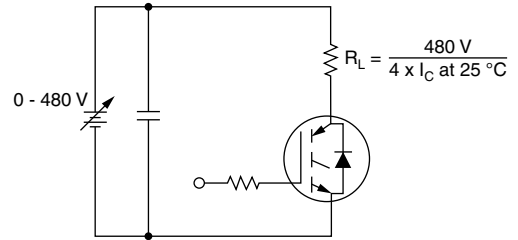
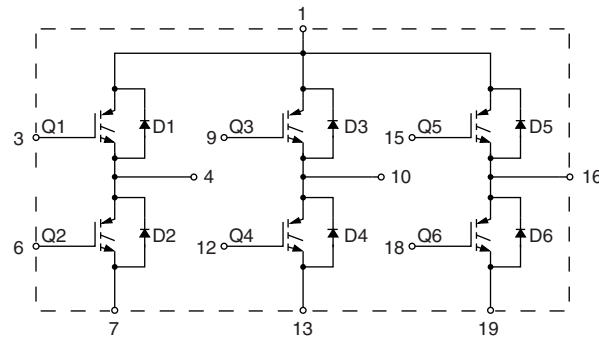


Fig. 20 - Pulsed Collector Current Test Circuit

**CIRCUIT CONFIGURATION**

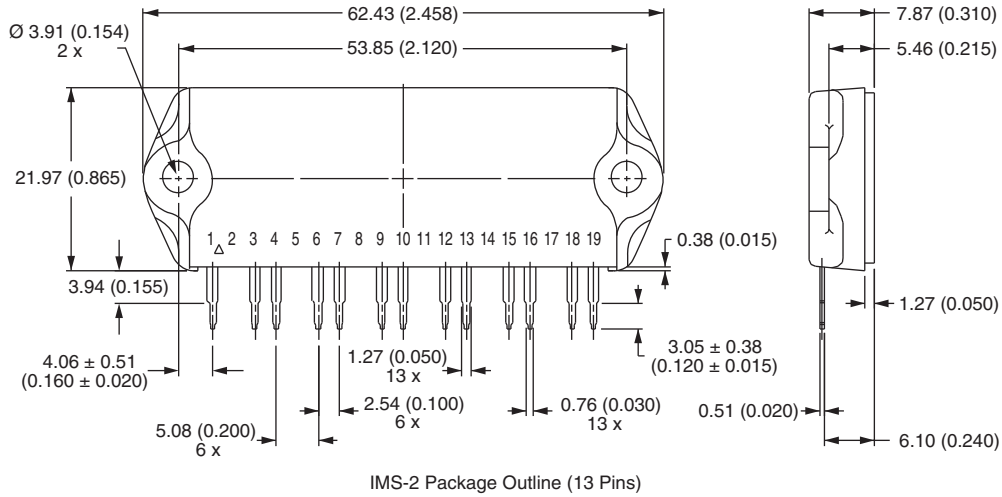


**LINKS TO RELATED DOCUMENTS**

<b>LINKS TO RELATED DOCUMENTS</b>	
Dimensions	<a href="http://www.vishay.com/doc?95066">www.vishay.com/doc?95066</a>

## IMS-2 (SIP)

**DIMENSIONS** in millimeters (inches)



### Notes

- (1) Tolerance unless otherwise specified  $\pm 0.254$  mm (0.010")
- (2) Controlling dimension: inch
- (3) Terminal numbers are shown for reference only



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